



Development and validation of a wide band Near Field Scan probe for the investigation of the radiated immunity of Printed Circuit Boards

André DURIER ^(1,2), *Sonia BENDHIA*⁽²⁾, *Tristan DUBOIS*⁽³⁾

(1) IRT Saint Exupery Toulouse, France

(2) LAAS-CNRS/INSA/Toulouse university, France

(3) IMS Bordeaux/Bordeaux university, France

1. INDUSTRIAL NEEDS AND OBJECTIVES

2. CONTEXT : NORMATIVE EMC TEST SET UP OVERVIEW

- Far field at equipment level : Radiated Immunity ISO 11452-2
- Near field at “component” level : NFS Immunity IEC TS62132-9

3. DEVELOPMENT AND VALIDATION OF SPECIFIC PROBES

- Specific Wide Band Immunity probes development : Initial requirements, design, field calculation
- Specific Wide band Immunity probes validation : induced voltage calculation, coupling factor requirement, coupling factor calculation & measurement, points to solve

4. CONCLUSION & PERSPECTIVES

INDUSTRIALS NEEDS

- The multiplication and the complexification of the electronic functions in the embedded systems dramatically increases the duration of the qualification tests and the **EMC non-compliance risk**.
- For economic reasons, the certified laboratories are obliged to work in 3 shifts and have less and **less qualified resources and time for the investigation of the problems during the test**.
- The **cost of the tests means** and the **qualified staff** for a normative test in **radiated immunity** is raised and constitutes a **bottleneck** for the equipment manufacturers.

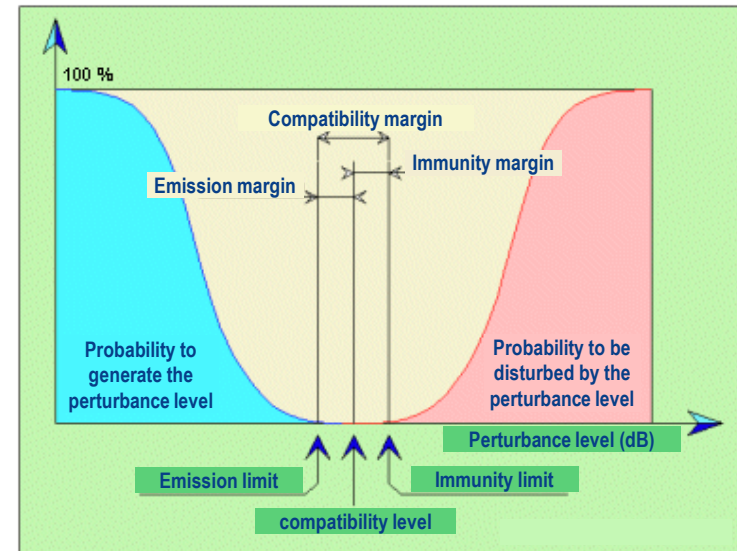


Figure source : A. Perez-Mas

To solve their problem, the equipment manufacturers need to have **fast, economic and easily usable investigation tools** allowing quick measurement of the level of susceptibility of their prototypes

The **Near Field Scan Immunity (NFSi)** method allows the **spatial localization** of **functional failures** caused by an electric and/or magnetic field generated by a probe placed nearby the component

- The objective is to propose a **new methodology of investigation of the radiated immunity** of electronic boards based on a **near field scanning** with the aim of detecting any problem before the normative qualification test

- The **main lock** lies in the **reliable extrapolation** of a **near-field measurements** for the **evaluation of a level of immunity in far field.**

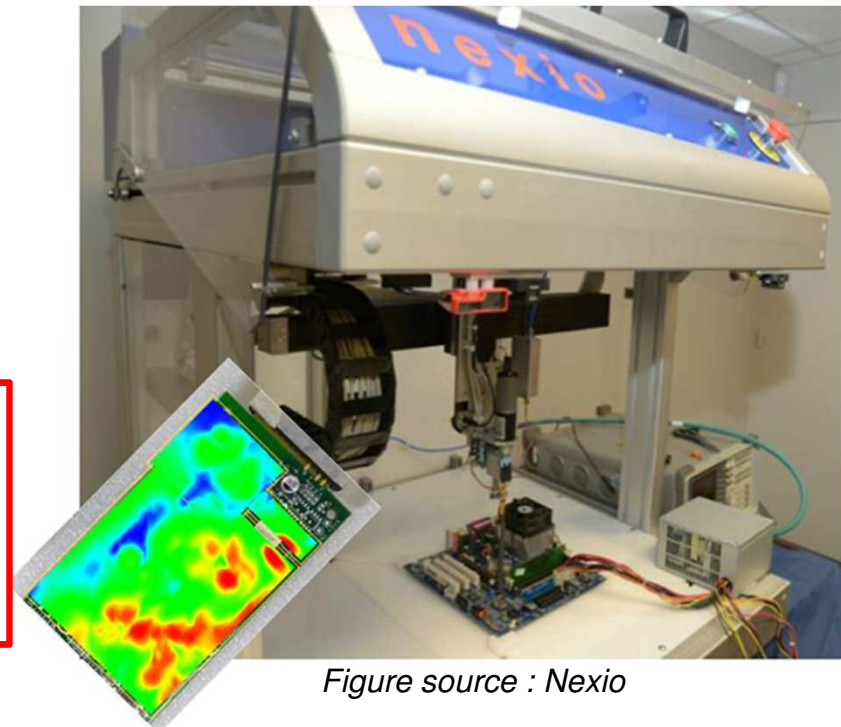


Figure source : Nexio

- To this end, a **modelling of the various normative tests** is necessary to make the **calculation of the electromagnetic fields** and the **calculation of induced currents at the PCB level**

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3. TOOLS AND METHODOLOGY

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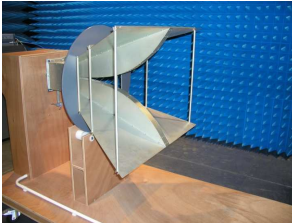
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Figure source : Continental Automotive



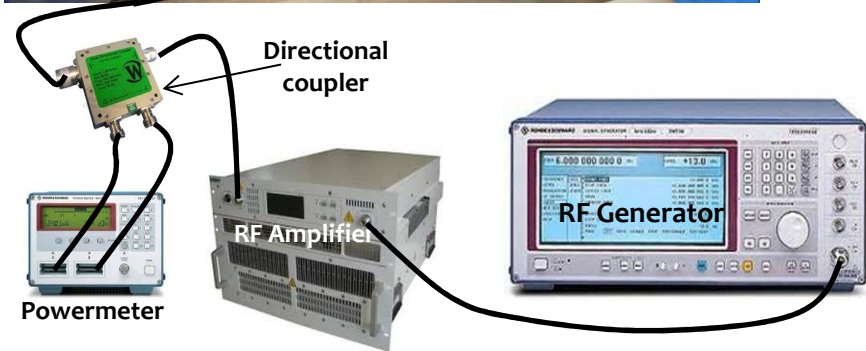
NORMATIVE EMC TEST ISO 11452-2 (ALSE) Radiated Immunity

ALSE test



Transducers

Antennas
 200 MHz-6 GHz automotive
 up to 18 GHz Aeronautics
 150 – 200 V/m typically in CW automotive
 200 – 490 V/m in CW aeronautics
 Up to 600 V/m (PM @2.7- 3.2 GHz automotive)
 Up to 7 200 V/m (PM @ 4-6 GHz aeronautics)



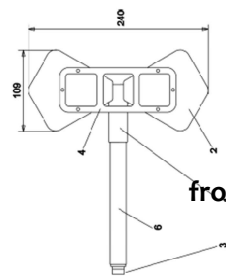
ISO 11452-5

Stripline
 100kHz-1GHz
 > 200V/m



ISO 11452-3

TEM cell
 100kHz-200MHz
 > 200V/m



ISO 11452-9

Portable transmitters
 Given frequency band
 from CB 26 MHz to IEEE 802.11a 5 850MHz
 Up to 300V/m @400MHz

NORMATIVE EMC TEST

IEC TS62132-9 Near Field Scan Immunity

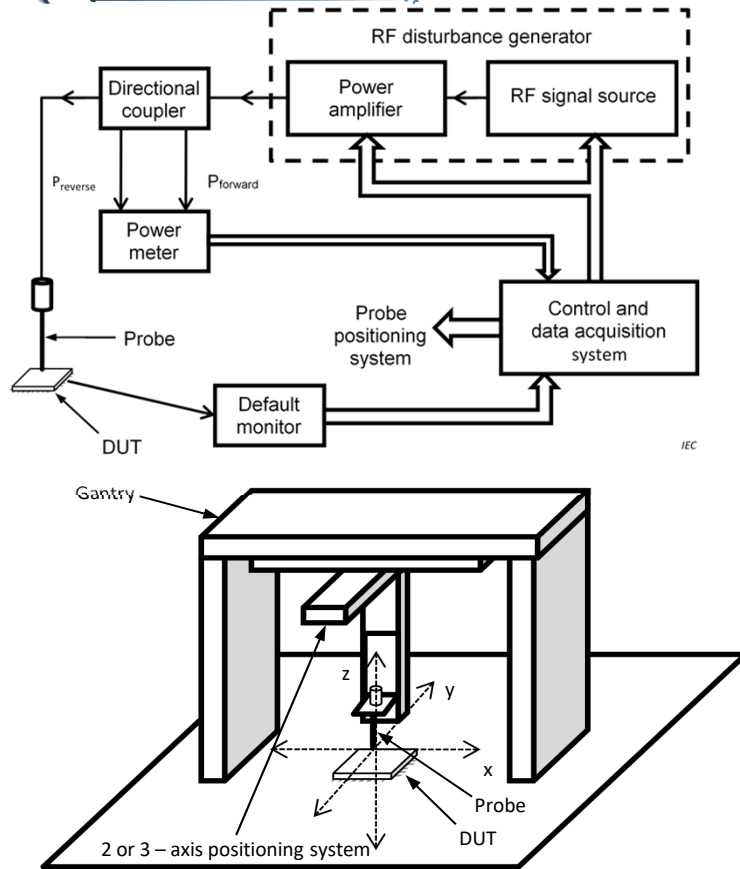


Figure source : IEC

« Radiated Susceptibility Investigation of electronic board from Near Field Scan method » N. Lacrampe, S. Serpaud, A. Boyer, S. Tran APEMC april 2010, Beijing (China)

« Application and limits of IC and PCB scanning methods for immunity analysis » D. Pommerenke, G. Muchaidze, J Koo, Q. Cai, J. Min proc. 18th int Zurich symposium on EMC Munich 2007

Frequency range (MHz)	0,15 to 1	1 to 100	100 to 1 000	1 000 to 6 000
Linear steps (MHz)	≤0,1	≤1	≤10	≤20
Logarithmic steps	≤5 % increment			

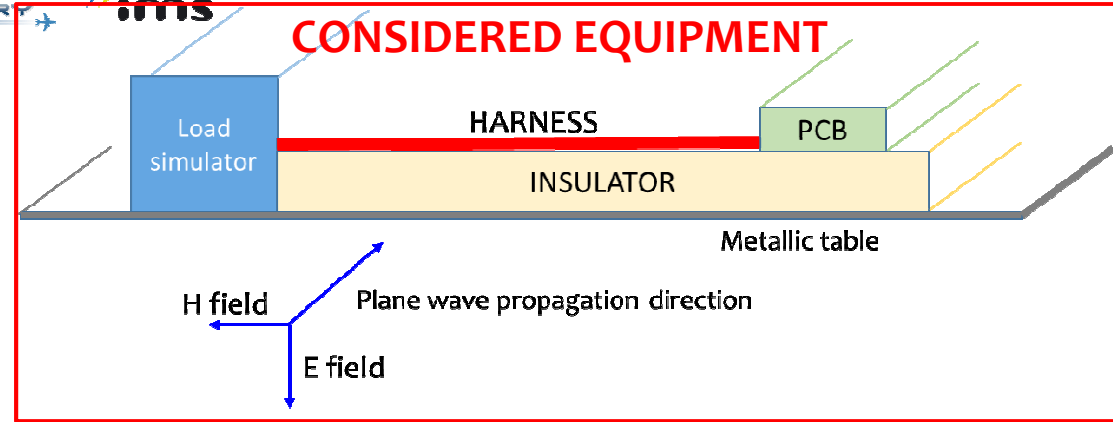
Pros

- **Contactless, no need of specific boards regardless Direct Power Injection**
- Standardized data exchange format (XML)
- More efficient than GTEM ISO 11452-3
- May avoid requalification in case of components obsolescence and second source

Cons :

- Dedicated and normalized for IC only
- **Test duration** : nb xyz positions x frequencies x dwell time => several hours
- **Probes performances limitations** (in low frequencies especially)
- Probe calibration method
- **Highlights failures not seen at the level system**

APPLIED METHODOLOGY



Far Field

Near Field

Simulation and measurement of the induced currents and voltages when the harness and electronic board are illuminated by a plane wave

Design of specific immunity probes

Simulation and measurement of the induced currents and voltages when an excitation signal is applied to the probe

Comparison of the current and voltage levels on a load placed on a PCB in far field and near field
Determination of the excitation signal level needed at the input of the probe to induce the same voltage level as in far field

Probe design improvement

Validation on industrial case (Op Amp application)

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SPECIFIC PROBES DEVELOPMENT

Initial requirements

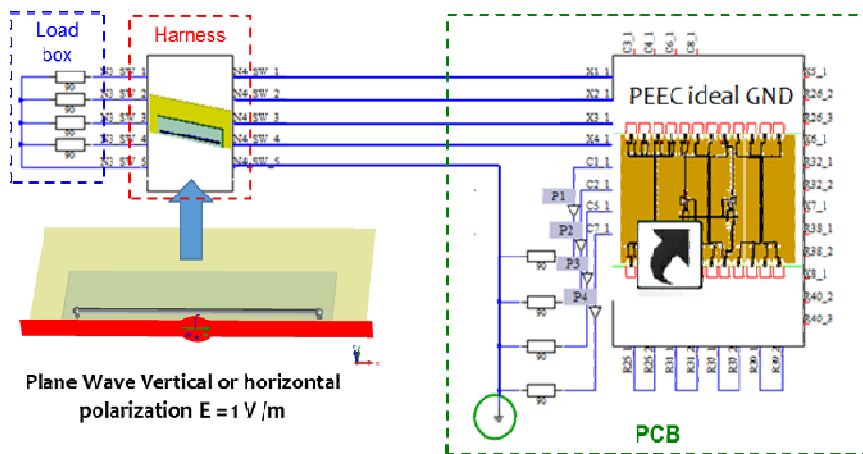
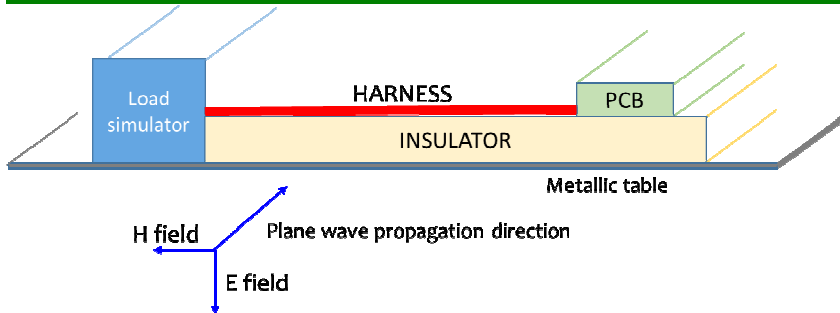
- **Requirement R#1 : Covering Area**
 - Probe must provide a E or H field covering a large area ($> 1 \text{ cm}^2$)
- **Requirement R#2 : Frequency band**
 - The frequency band covered by the probe must be [100 MHz- 3 GHz]
- **Requirement R#3 : Field**
 - R#3.0 : Field strength : one of the field components (normal or tangential) must be $> 500 \text{ V/m}$ for E-field and $> 1,4 \text{ A/m}$ for H-field (RMS value). **These values comes from an analysis of fields generated at PCB level during automotive and aeronautics radiated immunity tests at equipment level**
 - R#3.1 : To avoid spot effect, field uniformity must be $< -6 \text{ dB}$. The field uniformity is defined by the ratio standard deviation / median value calculated on the required covering area positioned at 1 mm of the probe. The field uniformity must be calculated for E field and H field in probe's normal and tangential plans @1 GHz.

Initial requirements are based on the hypothesis that aiming the same level of E or H-Field at PCB level than during a far field test is satisfying

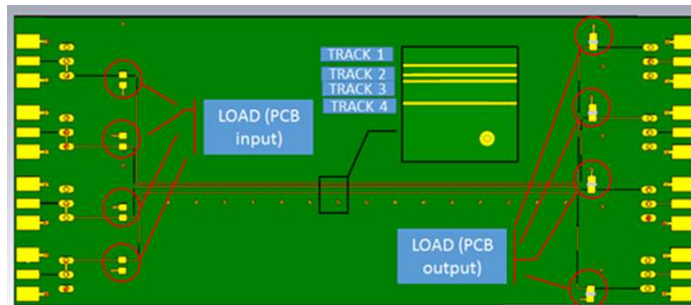
SPECIFIC PROBES DEVELOPMENT

Requirement on coupling factor (R#4.0)

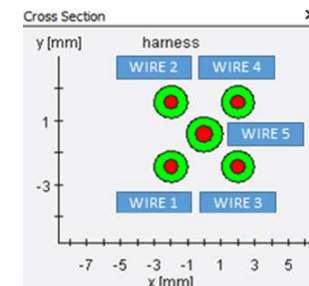
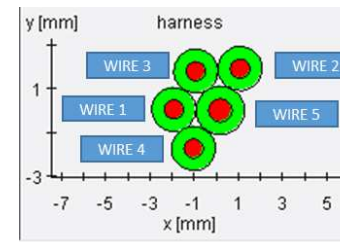
Coupling factor requirement is obtained from the calculation of induced voltages on a PCB load during harness irradiation using a parametric study



Plane Wave Vertical or horizontal polarization $E = 1 \text{ V/m}$

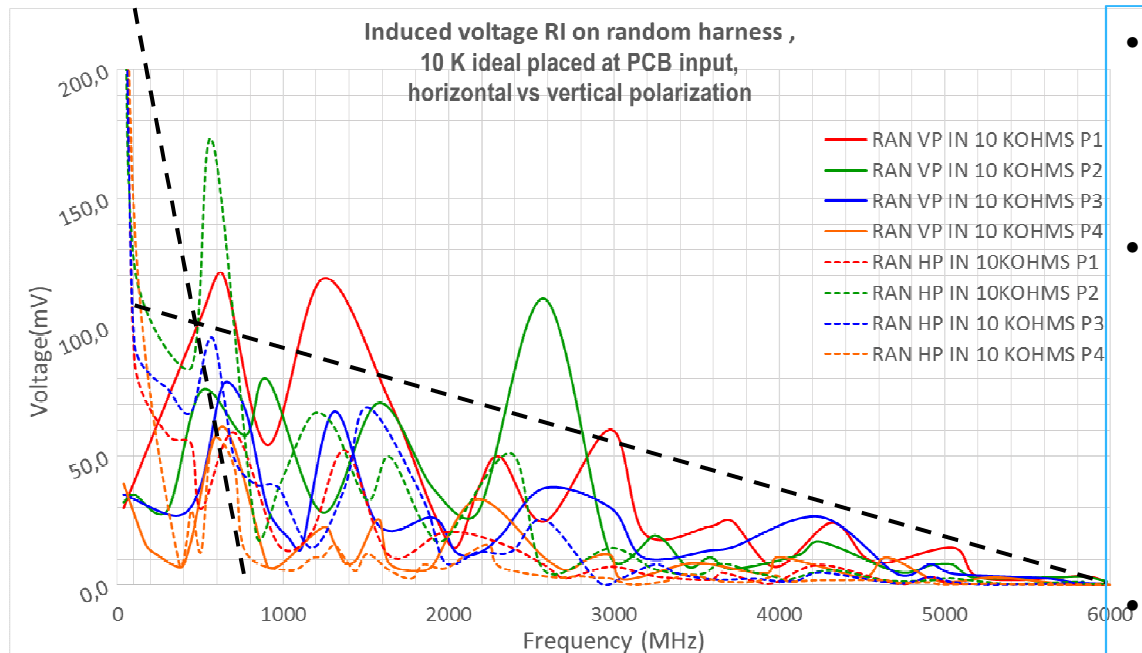


- **Modeling parameters**
- **Harness**
 - Number of wires into the harness : 5, 10, 20
 - Length : 1 500 , 1 800 mm
 - Section and wire rotation : regular without rotation, random with rotation
- **Plane wave**
 - Polarization : vertical, horizontal
- **Load box**
 - Loads : 90 Ω (ideal) fixed on all wires
- **Load PCB**
 - Placement : input, output
 - Values : 90 Ω (ideal) fixed all wires ; 10 k Ω (ideal) fixed all wires ; 10 Ω (ideal) fixed all wires ; Buffer IN, Buffer OUT, 10 pF, 100 pF, 1 nF



SPECIFIC PROBES DEVELOPMENT

Requirement on coupling factor (R#4.0)



Trend curve equation

	Frequency	
	100 – 500 MHz	500 – 3000 MHz
Required PCF	$- 2.5 \cdot 10^{-4} F(\text{MHz}) + 0.225$	$- 1.82 \cdot 10^{-5} F(\text{MHz}) + 0.109$

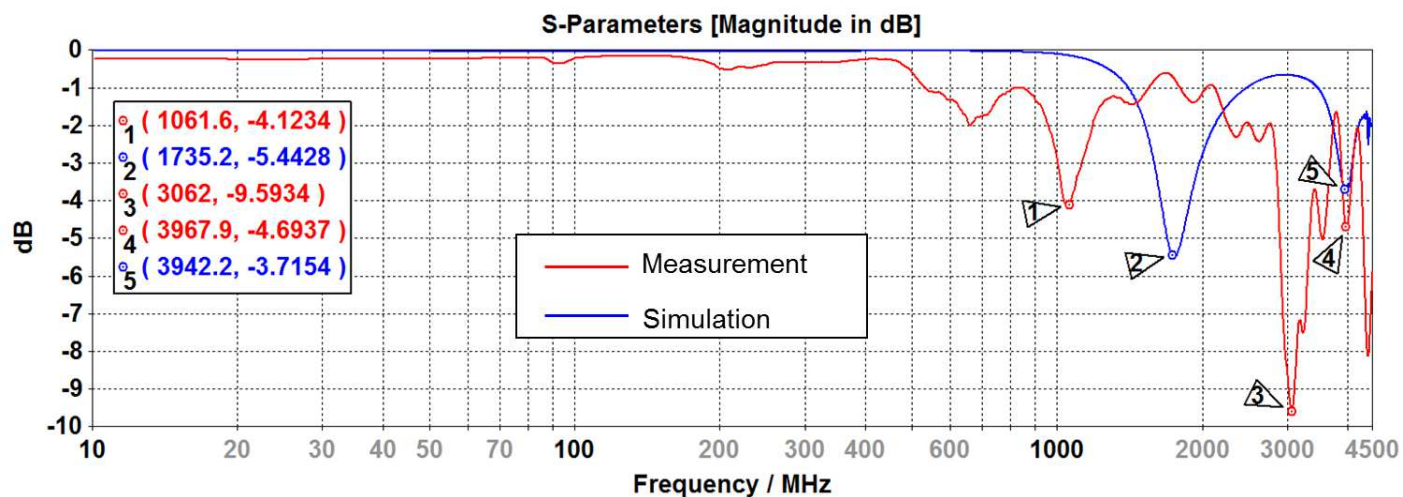
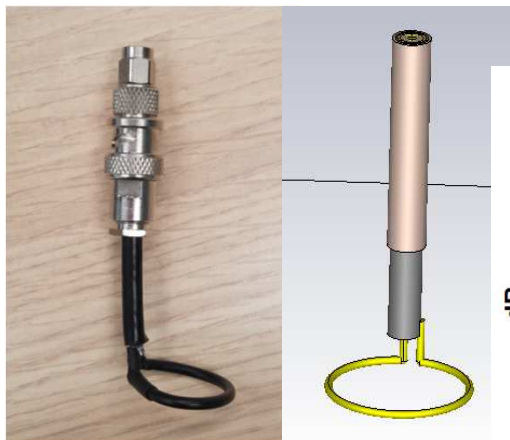
- **The value of the load on the PCB has the higher influence :** Higher is load impedance, higher will be the induced voltage
 - **Harness resonances** are observable at frequencies corresponding to electric length = $(2n + 1) \cdot \lambda / 4$ where λ correspond to the harness length (not seen on the figure because envelop curves are taken)
- The voltages induced by the **direct irradiation of the PCB are negligible** compared to those generated by harness irradiation

Assuming in first approximation required coupling factor = Induced voltage / applied voltage

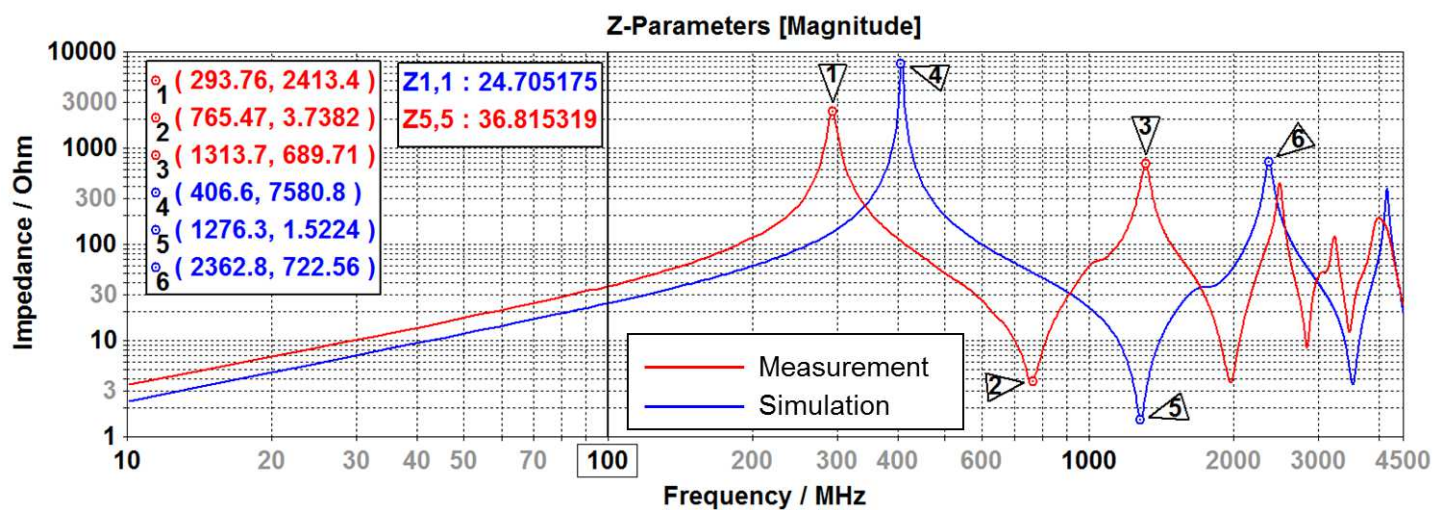
A trend curve could be extracted from worst case saying **whatever the real load, plane wave polarization and harness will be, the induced voltage will not overtake this limit**

SPECIFIC PROBES DEVELOPMENT

Wire loop H-field probe design

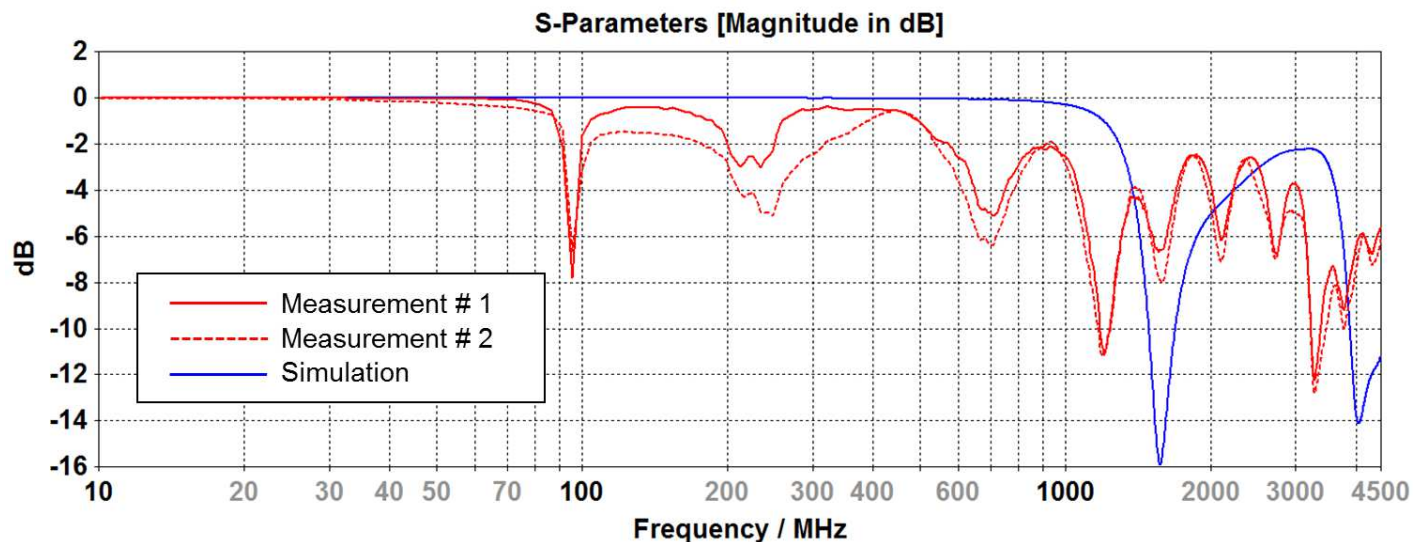


INDUCTIVE COUPLING

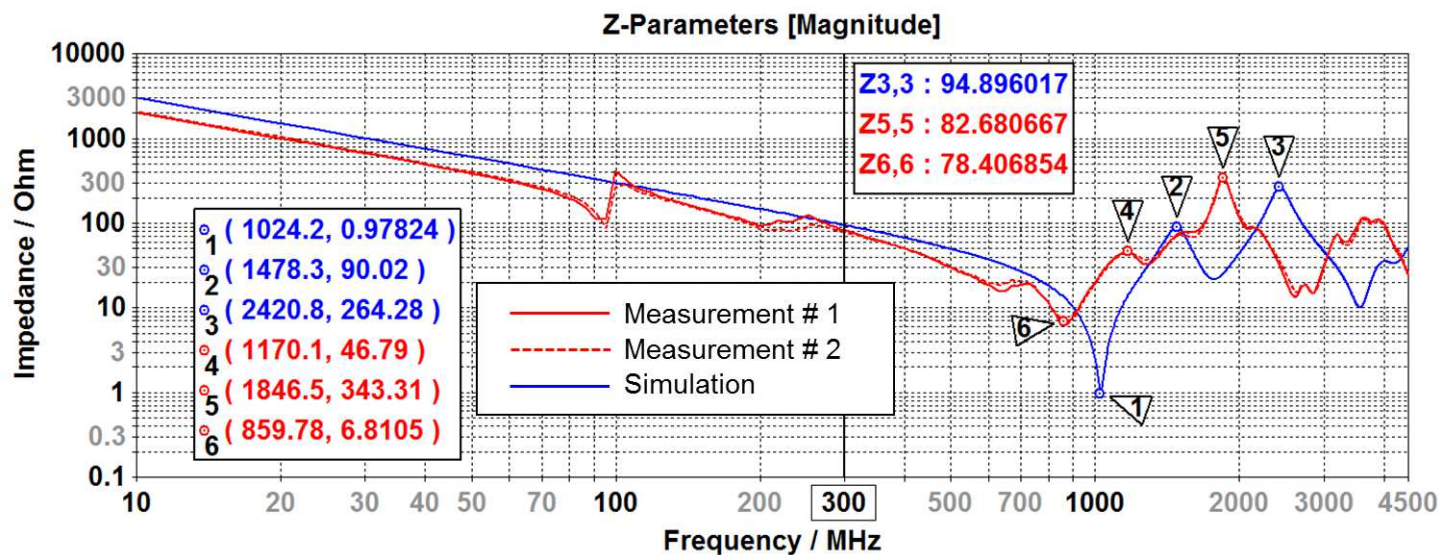


SPECIFIC PROBES DEVELOPMENT

conical E-field probe design

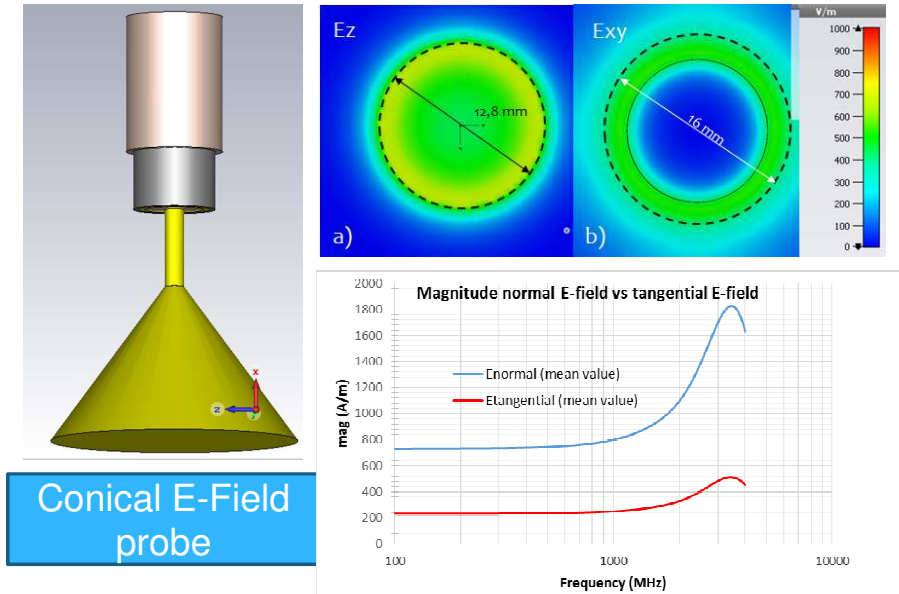
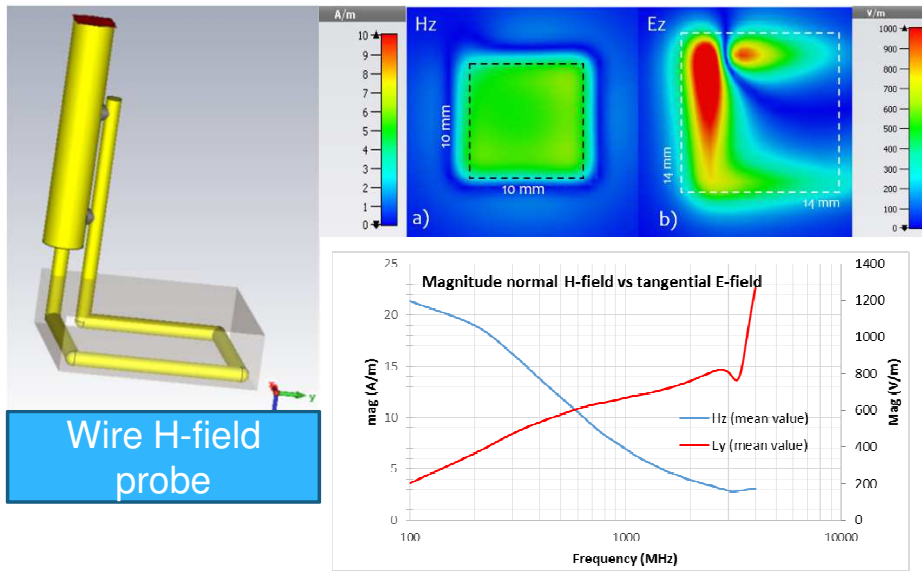


CAPACITIVE COUPLING



SPECIFIC PROBES DEVELOPMENT

Initial requirements validation



Wire H-field Probe

Pros

- High H_z field strength 7.38 A/m@1 GHz
- Homogeneity of H_z field

Cons

- Inhomogeneity of E_z and E_{xy} fields (spot effect)

Conical E-field Probe

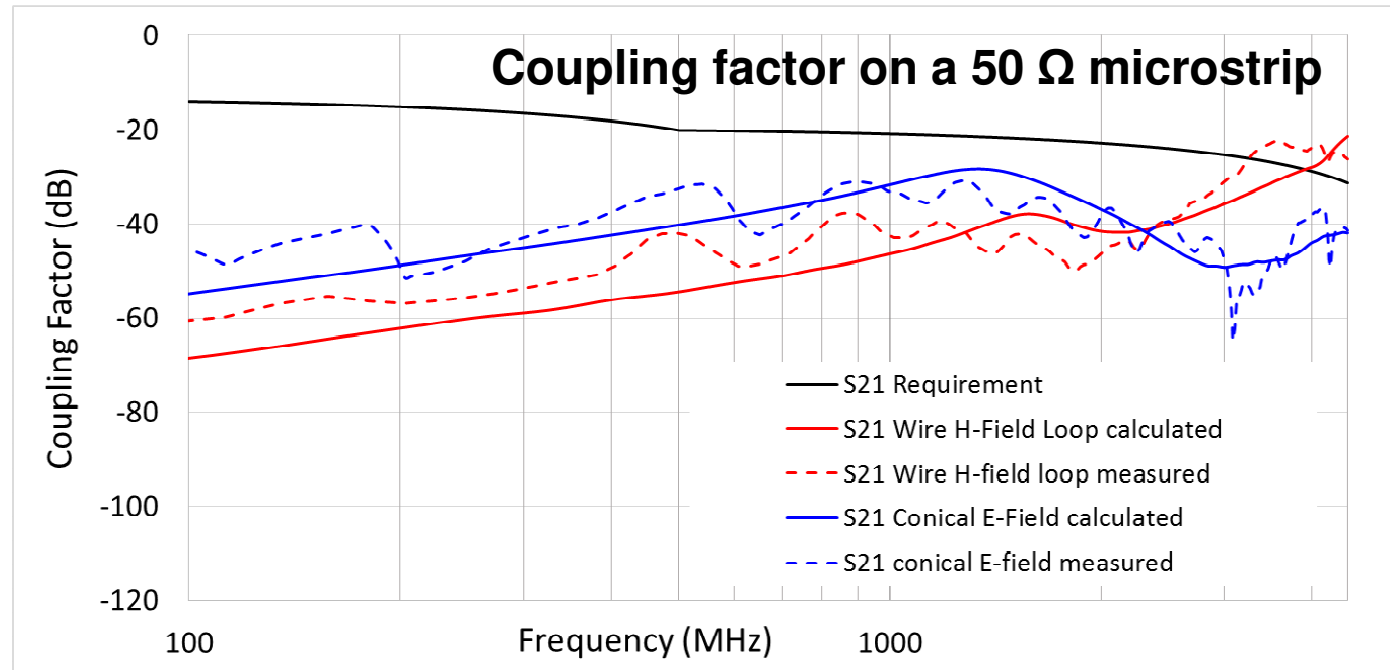
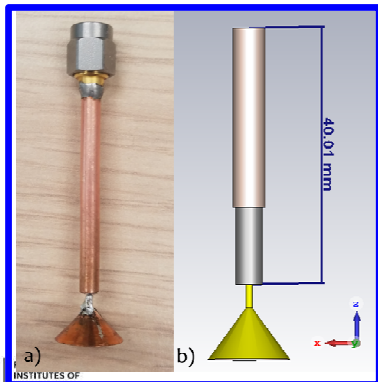
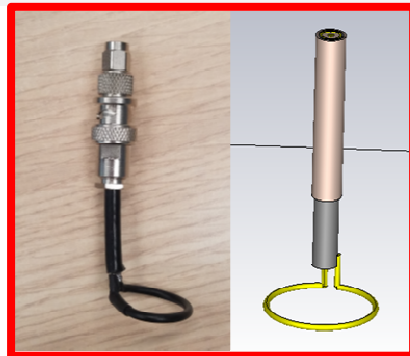
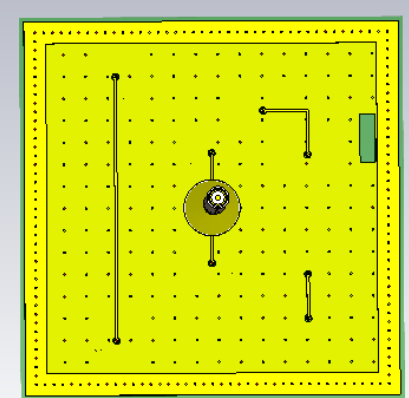
Pros

- High E_z -field strength 800 V/m@1 GHz
- Homogeneity of E_z -Field
- Negligible H-Field

No Cons

SPECIFIC PROBES DEVELOPMENT

coupling factor validation



Conical E probe shows the best coupling factor from 100 MHz up to 2 GHz.
Wire H-Field probe shows the best coupling factor above 2 GHz

Coupling factor between 100- 800 MHz is low (< - 40 dB)

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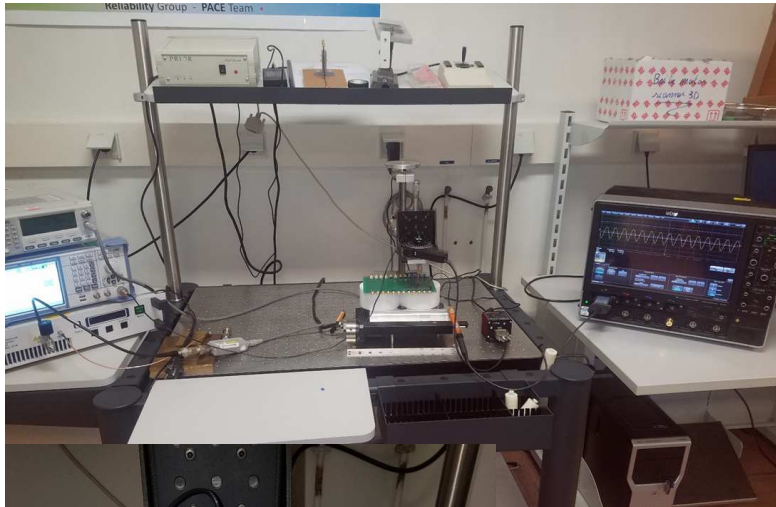
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CONCLUSION

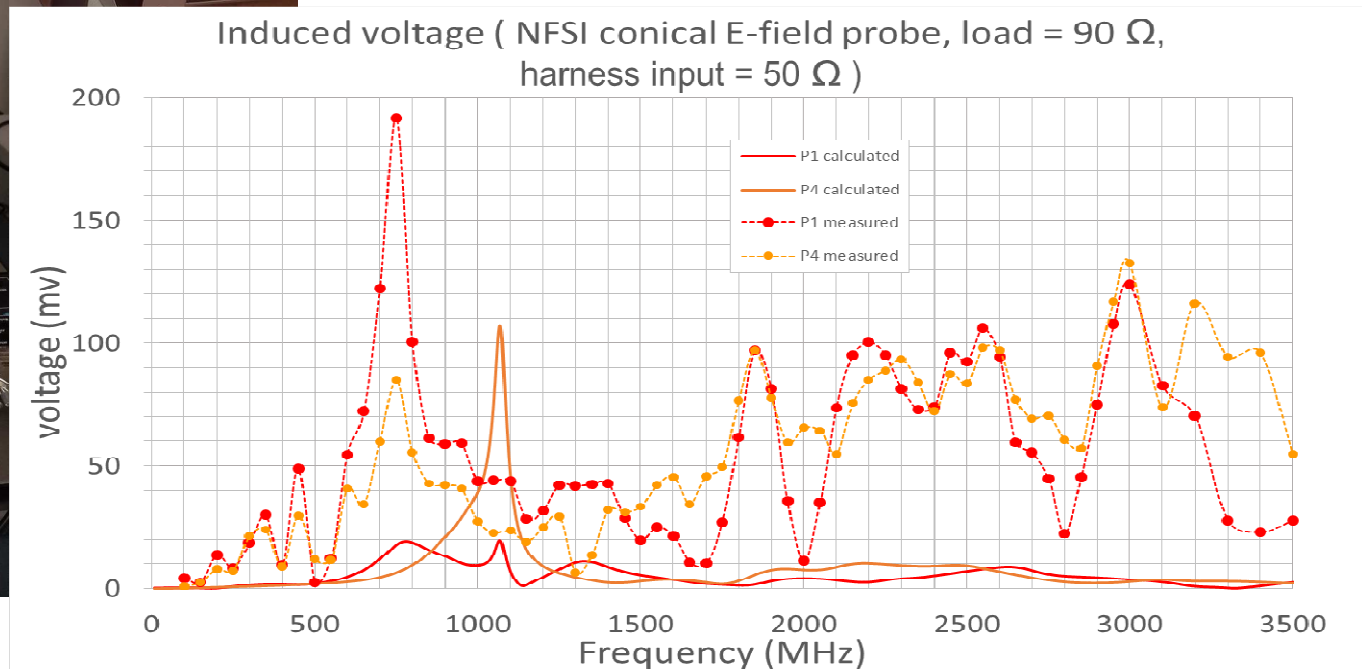
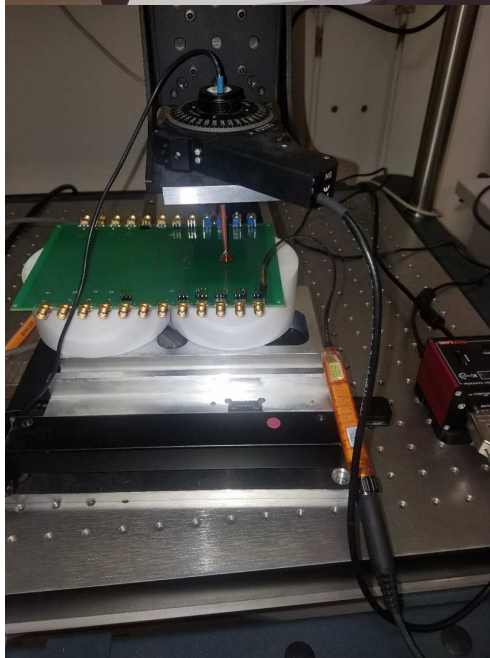
Calculation of the induced voltages



Voltages measured with a differential probe on a 90Ω load placed on PCB demonstrator

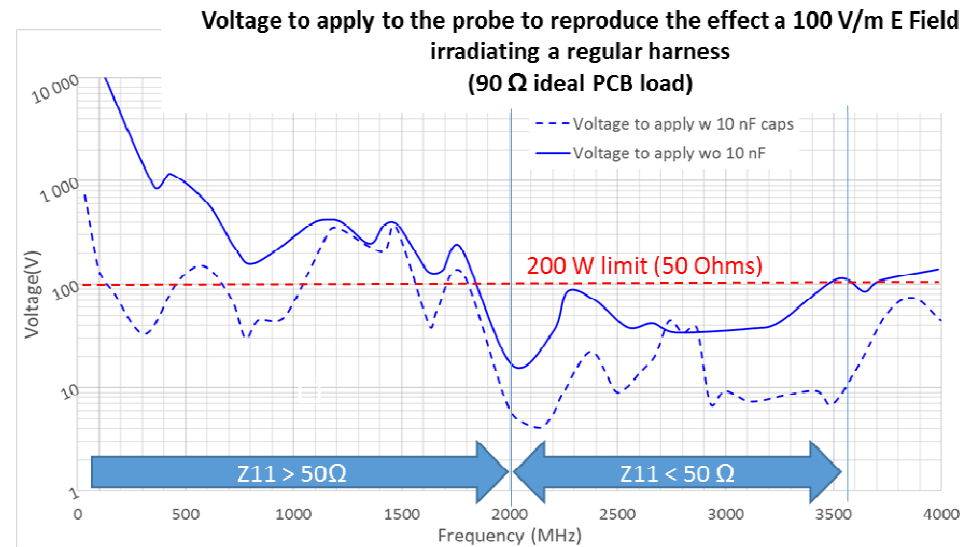
- The measurements are higher than the calculation seems indicating a better coupling than expected ?

High discrepancies between the calculation and the measurements



CONCLUSION & PERSPECTIVES

- A Probe Coupling Factor requirement has been originally determined from Far Field simulation at equipment level
- Some probe design have been compared in term of radiated field strength and homogeneity and in term of coupling factor on 50 Ω microstrip



ISSUES TO SOLVE

- Measured and modeled **probe coupling factor are far away from the requirement**
- Consequently, **the necessary power** to be applied on the probe to reproduce the effect of a 100 V/m E-field **is practically not reachable** in an **affordable** way : adding filtering capacitors at connector level will be helpful but **PCF must be improved for $F < 1$ GHz**
- **Discrepancies between measurements and simulation must be solved**



Thanks for your attention

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